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I. IN THE CLAIMS

This listing of claims will replace all prior versions. Please amend claims 8 and 14 as shown.

1. – 7. (Canceled)

8. (Previously Presented) A method of etching and cleaning a TiW alloy layer comprising:
providing a substrate comprising an exposed TiW alloy layer and further
comprising at least one of Al, Cu, or an AlCu alloy;
etching the TiW alloy by a method which results in formation of etching residue;
contacting the substrate with a TiW-selective composition comprising water and
between about 7.5% to about 15% by weight of periodic acid, wherein the composition is
effective in removing said TiW alloy and removing residues of etching of TiW alloy, wherein
the removal rate of the TiW alloy and residue thereof is greater than a removal rate of Al, Cu, or
an AlCu alloy, and wherein the pH of the composition is less than 7, for a time and at a
temperature sufficient to cause the composition to remove at least a portion of the TiW alloy and
substantially all of the etching residue from the substrate; and
rinsing the substrate, wherein said composition does not include abrasives.

9. (Previously Presented) The method of claim 8, wherein the substrate further comprises an
exposed AlCu alloy, wherein by removing a relatively small amount of Al, Cu, or an AlCu alloy
means the specificity of removal of TiW to AlCu, in terms of etch rate, is at least about 3.

10. (Previously Presented) The method of claim 9, wherein the substrate further comprises an
exposed AlCu alloy, wherein the specificity of removal of TiW to AlCu, in terms of etch rate, is
at least about 5.

11. (Previously Presented) The method of claim 10, wherein the substrate further comprises
an exposed AlCu alloy, wherein the specificity of removal of TiW to AlCu, in terms of etch rate,
is at least about 7.